



2SA1419/2SC3649

High-Voltage Switching Applications

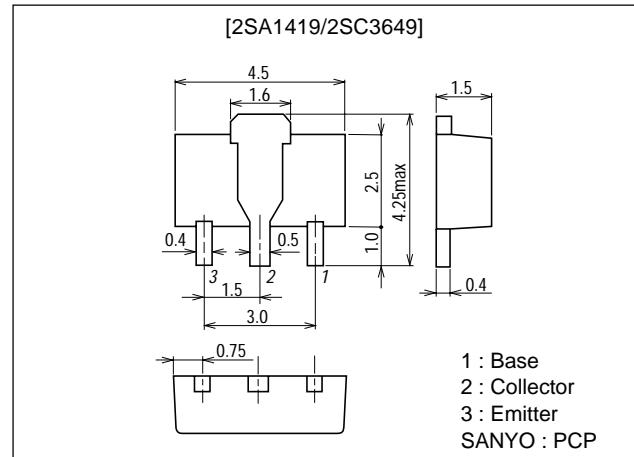
Features

- Adoption of FBET, MBIT processes.
- High breakdown voltage and large current capacity.
- Ultrasmall size making it easy to provide high-density hybrid ICs.

Package Dimensions

unit:mm

2038A



() : 2SA1419

Specifications

Absolute Maximum Ratings at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V_{CB0}		(-)180	V
Collector-to-Emitter Voltage	V_{CEO}		(-)160	V
Emitter-to-Base Voltage	V_{EBO}		(-)6	V
Collector Current	I_C		(-)1.5	A
Collector Current (Pulse)	I_{CP}		(-)2.5	A
Collector Dissipation	P_C		500	mW
		Moutned on ceramic board (250mm ² ×0.8mm)	1.5	W
Junction Temperature	T_j		150	°C
Storage Temperature	T_{stg}		-55 to +150	°C

Electrical Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	I_{CBO}	$V_{CB} = (-)120\text{V}, I_E = 0$			(-)1	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = (-)4\text{V}, I_C = 0$			(-)1	μA
DC Current Gain	h_{FE1}	$V_{CE} = (-)5\text{V}, I_C = (-)100\text{mA}$	100*		400*	
	h_{FE2}	$V_{CE} = (-)5\text{V}, I_C = (-)10\text{mA}$	80			

* : The 2SA1419/2SC3649 are classified by 100mA h_{FE} as follows :

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Rank	R	S	T
h_{FE}	100 to 200	140 S 280	200 to 400

Marking 2SA1419 : AE
2SC3649 : CE h_{FE} rank : R, S, T

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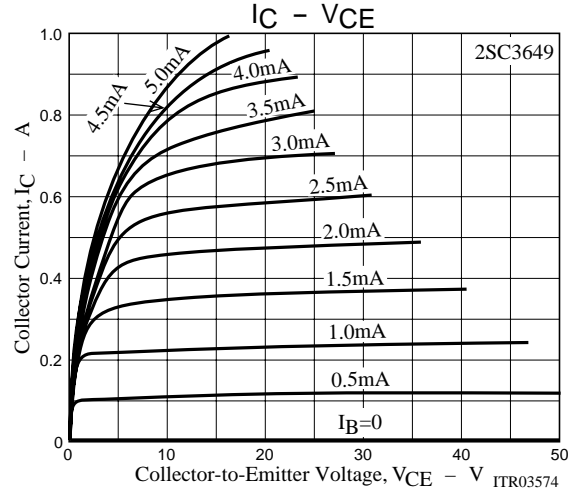
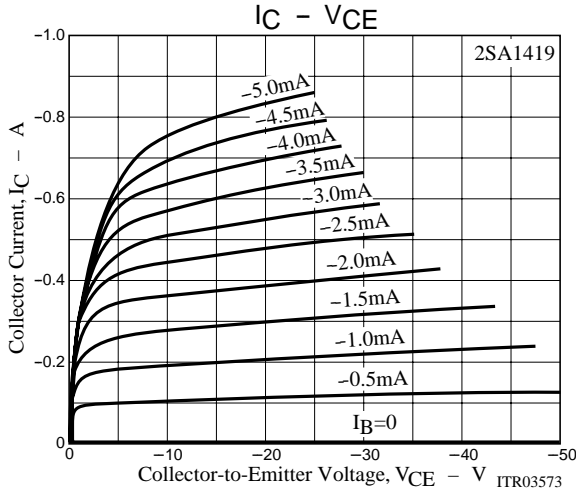
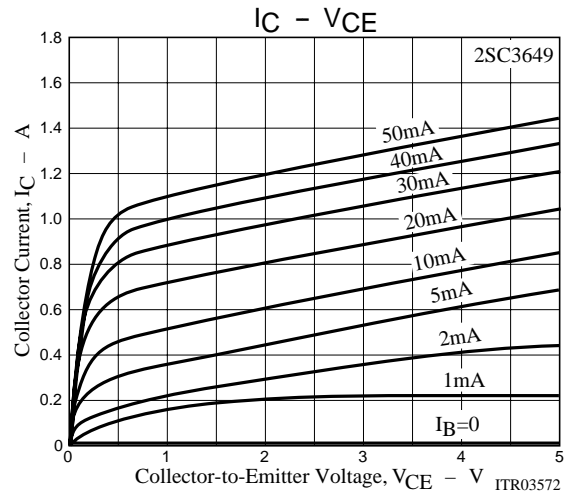
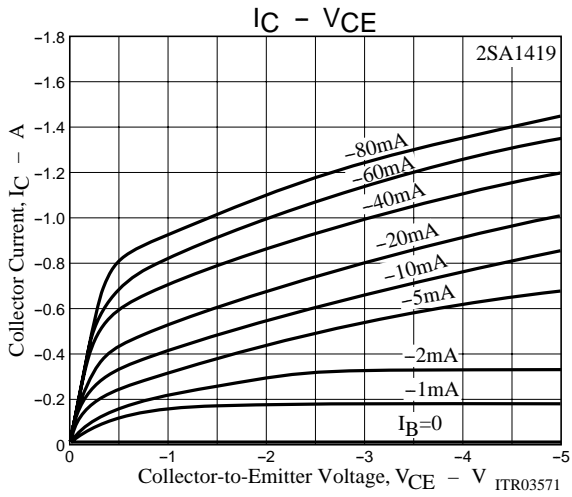
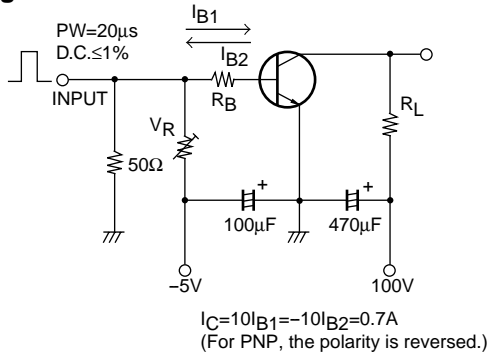
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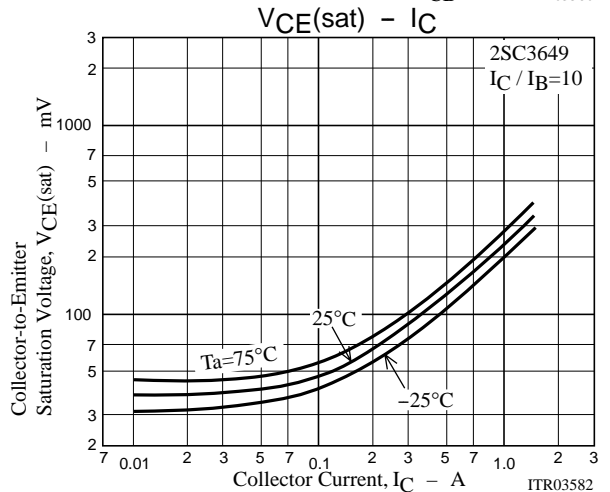
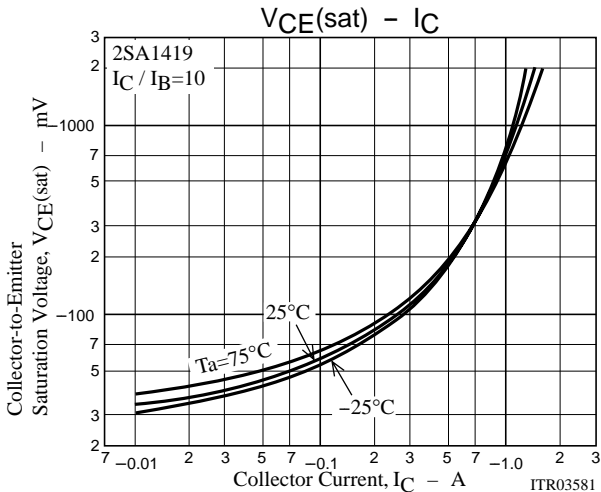
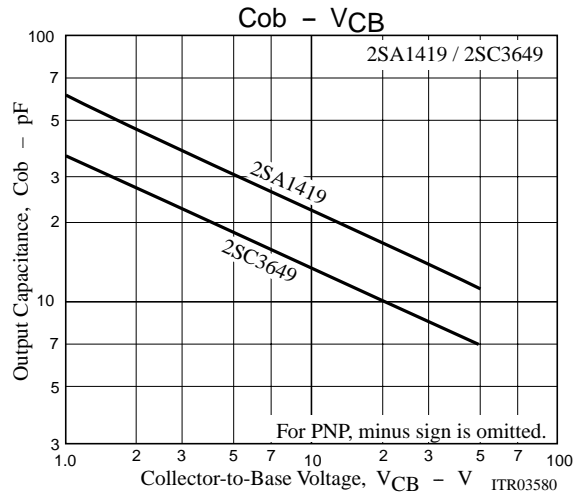
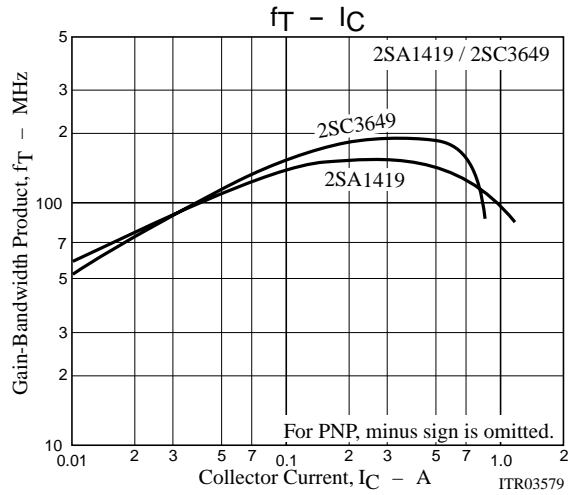
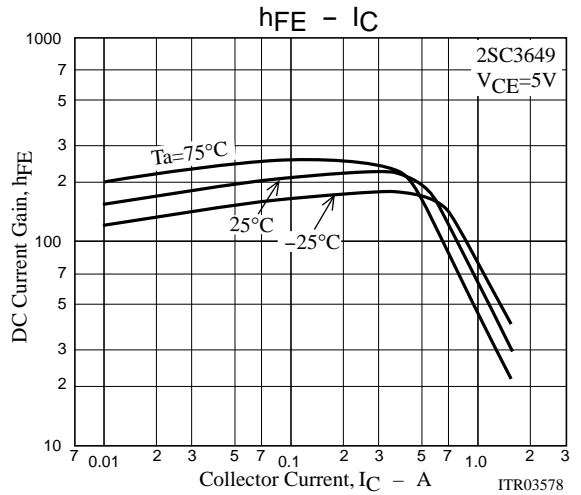
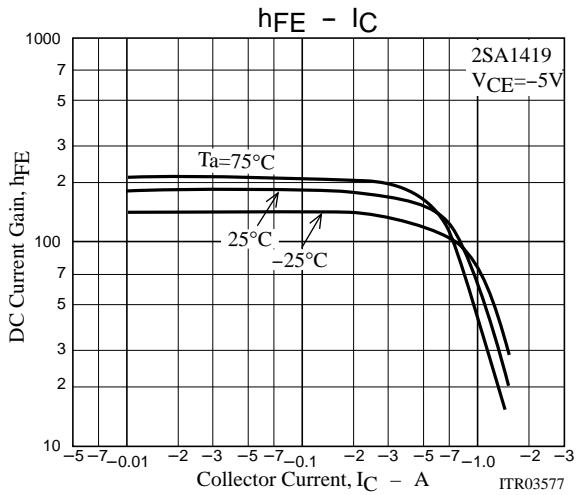
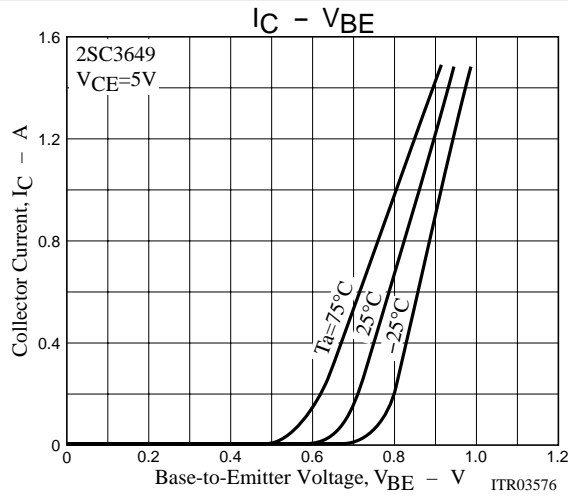
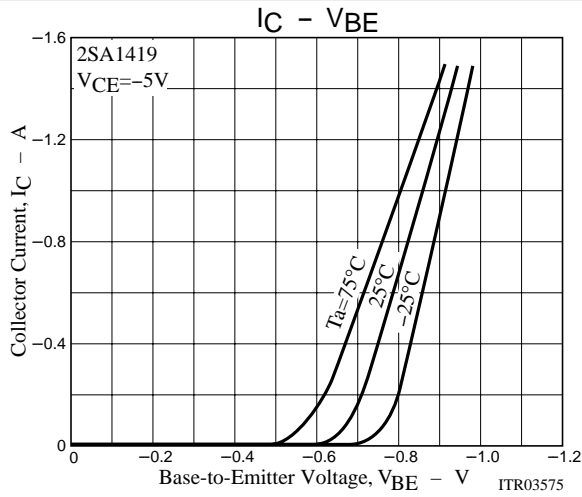
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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Gain-Bandwidth Product	f_T	$V_{CE}=(-)10V, I_C=(-)50mA$		120		MHz
Output Capacitance	C_{ob}	$V_{CB}=(-)10V, f=1MHz$		(22)		pF
				14		pF
Collector-to-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=(-)500mA, I_B=(-)50mA$		(-200)	(-500)	mV
				130	450	mV
Base-to-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=(-)500mA, I_B=(-)50mA$		(-0.85)	(-1.2)	V
Collector-to-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C=(-)10\mu A, I_E=0$	(-)	180		V
Collector-to-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=(-)1mA, R_{BE}=\infty$	(-)	160		V
Emitter-to-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E=(-)10\mu A, I_C=0$	(-)	6		V
Turn-ON Time	t_{on}	See specified Test Circuit.		(40)		ns
				40		ns
Storage Time	t_{stg}	See specified Test Circuit.		(0.7)		μs
				1.2		μs
Fall Time	t_f	See specified Test Circuit.		(40)		ns
				80		ns

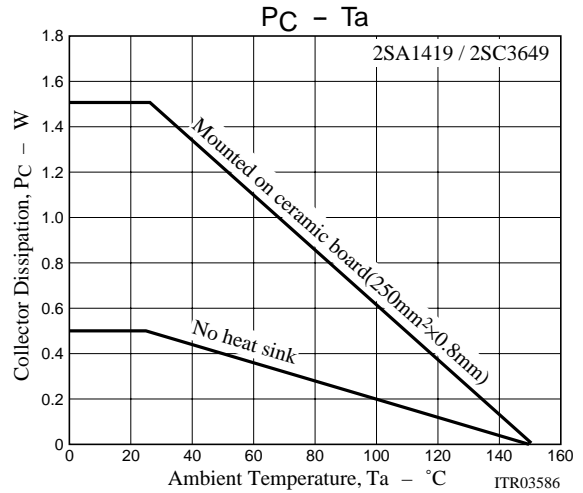
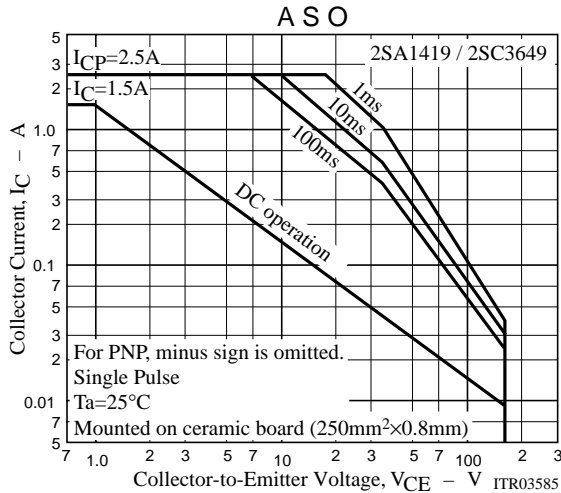
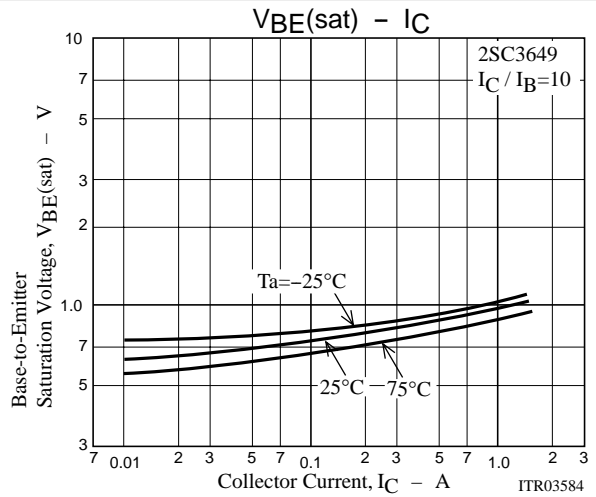
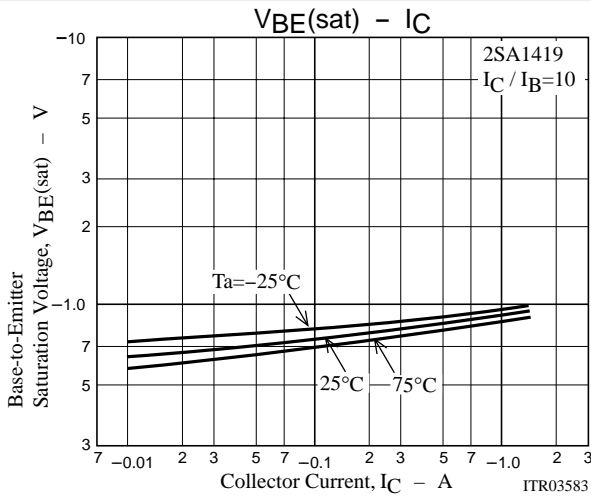
Switching Time Test Circuit



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